Product data sheet

1. General description

NPN low VCEsat transistor in a SOT89 (SC-62/TO-243) small and flat lead Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS5520X

2. Features and benefits

- High h_{FE} and low V_{CEsat} at high current operation
- High collector current capability: I_C maximum 5 A
- Higher efficiency leading to less heat generation
- AEC-Q101 qualified

3. Applications

- · Medium power peripheral drivers, e.g. fans and motors
- · Strobe flash units for DSC and mobile phones
- · Inverter applications, e.g. TFT displays
- · Power switch for LAN and ADSL systems
- Medium power DC-to-DC conversion
- Battery chargers

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	20	V
I _C	collector current		-	-	5	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	10	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = 5 A; I_B = 500 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	32	44	mΩ

5. Pinning information

Table 2. Pinning information

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Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter		С
2	С	collector		
3	В	base	3 2 1	B — (
			SOT89	sym123



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6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PBSS4520X	SOT89	plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body	SOT89		

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBSS4520X	%1F

[1] % = placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

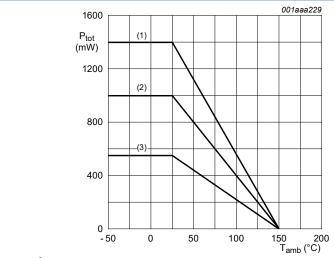
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	20	V
V _{CEO}	collector-emitter voltage	open base		-	20	V
V _{EBO}	emitter-base voltage	open collector		-	5	V
I _C	collector current			-	5	Α
I _{CRM}	repetitive peak collector current		[1] [2]	-	7	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	10	Α
I _B	base current			-	1	А
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms		-	2	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[2] [3]	-	2.5	W
			[2]	-	0.55	W
			[4]	-	1	W
			[5]	-	1.4	W
			[6]	-	1.6	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Operated under pulsed conditions: pulse width $t_p \le 10$ ms; duty cycle $\delta \le 0.2$.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Operated under pulsed conditions: $t_p \le 10$ ms; $\delta \le 0.2$.
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm²
- [5] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [6] Device mounted on a 7 cm² ceramic PCB, 1 cm² single-sided copper and tin-plated.

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- (1) FR4 PCB; 6 cm² mounting pad for collector (2) FR4 PCB; 1 cm² mounting pad for collector
- (3) FR4; standard footprint

Power derating curves Fig. 1.

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	[1] [2] [3] [4] [5]	[1] [2]	-	-	50	K/W
	junction to ambient		[1]	-	-	225	K/W
			[3]	-	-	125	K/W
			[4]	-	-	90	K/W
			[5]	-	-	80	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	16	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Operated under pulsed conditions: $t_p \le 10$ ms; $\delta \le 0.2$. Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm². Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm². [3]
- [4]
- Device mounted on a 7 cm² ceramic PCB, 1 cm² single-sided copper and tin-plated.

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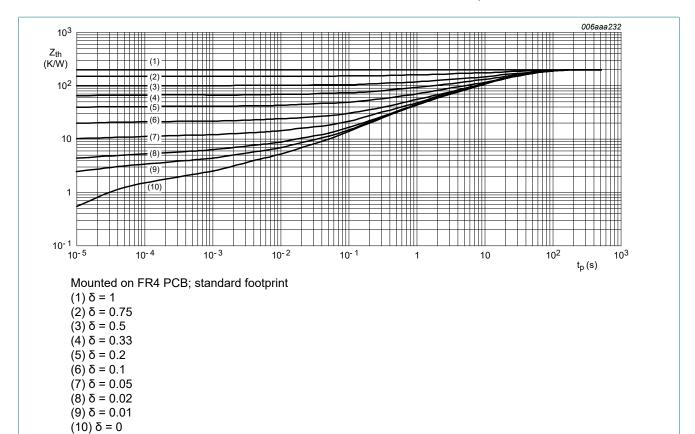
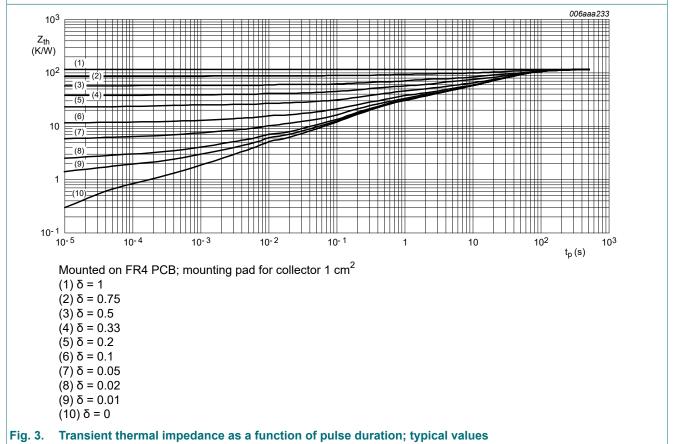
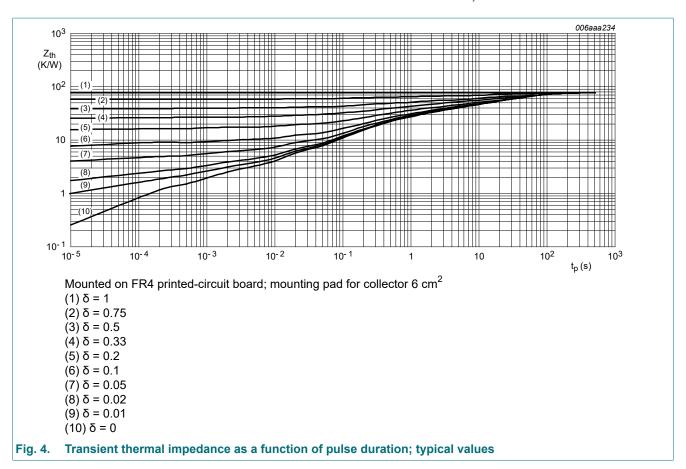


Fig. 2. Transient thermal impedance as a function of pulse duration; typical values



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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{СВО}	collector-base cut-off	V _{CB} = 20 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 20 V; I _E = 0 A; T _j = 150 °C	-	-	50	μΑ
ЕВО	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
CES	collector-emitter cut-off current	V _{CE} = 20 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 2 V; I _C = 0.5 A; T _{amb} = 25 °C	300	450	-	
		V_{CE} = 2 V; I_{C} = 1 A; pulsed; $t_{p} \le 300 \ \mu s$; δ ≤ 0.02; T_{amb} = 25 °C	300	440	-	
		V_{CE} = 2 V; I_{C} = 2 A; pulsed; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	250	420	-	
		V_{CE} = 2 V; I_{C} = 5 A; pulsed; $t_{p} \le 300 \ \mu s$; δ ≤ 0.02; T_{amb} = 25 °C	200	380	-	
V _{CEsat}	collector-emitter saturation voltage	I _C = 0.5 A; I _B = 5 mA; T _{amb} = 25 °C	-	35	50	mV
		I _C = 1 A; I _B = 10 mA; T _{amb} = 25 °C	-	50	70	mV
		I_C = 2.5 A; I_B = 125 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	85	120	mV
		I_C = 4 A; I_B = 200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	130	180	mV
		I_C = 5 A; I_B = 500 mA; pulsed; $t_p \le$	-	160	220	mV
R _{CEsat}	collector-emitter saturation resistance	300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	32	44	mΩ
V _{BEsat}	base-emitter saturation voltage	I_C = 4 A; I_B = 200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	0.9	1.05	V
		I_C = 5 A; I_B = 500 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	0.96	1.1	V
V_{BEon}	base-emitter turn-on voltage	V _{CE} = 2 V; I _C = 2 A; T _{amb} = 25 °C	-	0.74	0.85	V
fт	transition frequency	V_{CE} = 10 V; I_{C} = 100 mA; f = 100 MHz; T_{amb} = 25 °C	100	125	-	MHz
C _c	collector capacitance	V_{CB} = 10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C	-	90	110	pF

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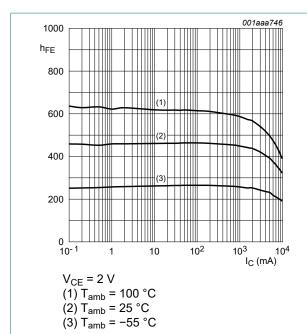


Fig. 5. DC current gain as a function of collector current; typical values

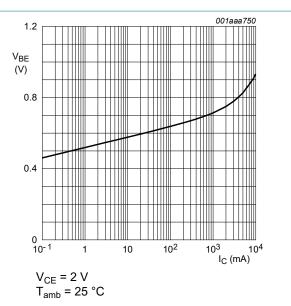


Fig. 6. Base-emitter voltage as a function of collector current; typical values

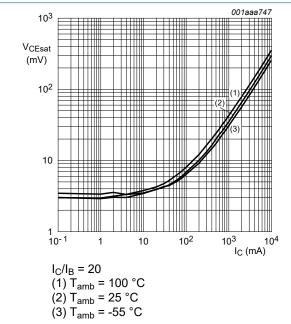


Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values

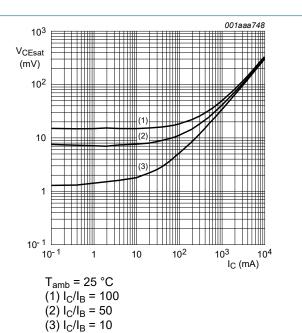


Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

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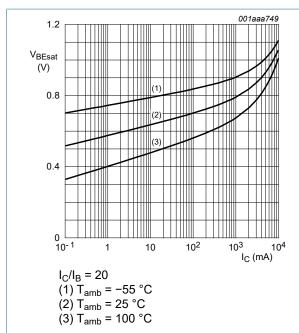
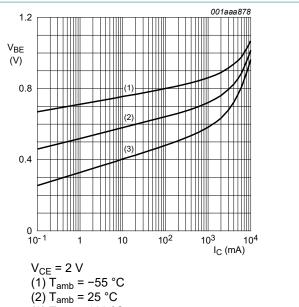
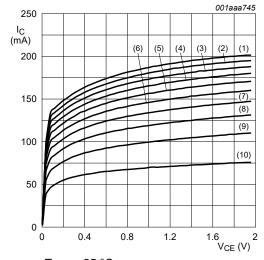


Fig. 9. Base-emitter saturation voltage as a function of Fig. 10. Base-emitter voltage as a function of collector collector current; typical values



(3) $T_{amb} = 100 \, ^{\circ}C$

current; typical values



T_{amb} = 25 °C

(1) $I_B = 5 \text{ mA}$

 $(2) I_B = 4.5 \text{ mA}$

(3) $I_B = 4 \text{ mA}$

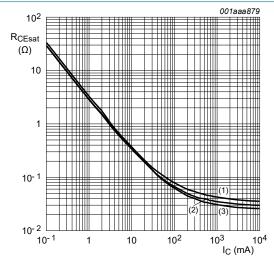
(4) $I_B = 3.5 \text{ mA}$

(5) $I_B = 3 \text{ mA}$ (6) $I_B = 2.5 \text{ mA}$ (7) $I_B = 2 \text{ mA}$

(8) $I_B = 1.5 \text{ mA}$ (9) $I_B = 1 \text{ mA}$

(10) $I_B = 0.5 \text{ mA}$

Fig. 11. Collector current as a function of collectoremitter voltage; typical values



 $I_{\rm C}/I_{\rm B} = 20$

(1) T_{amb} = 100 °C

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig. 12. Equivalent on-resistance as a function of collector current; typical values

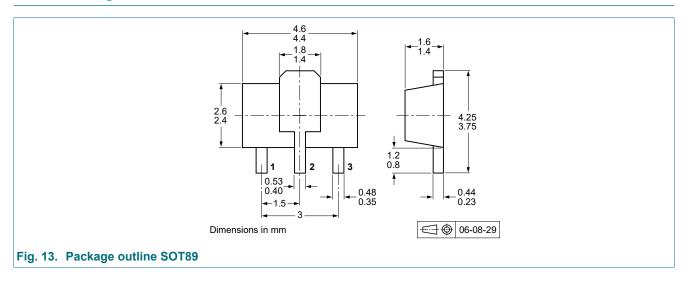
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11. Test information

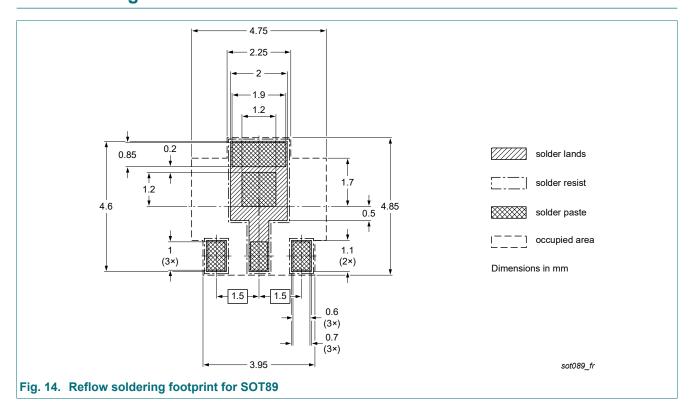
Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

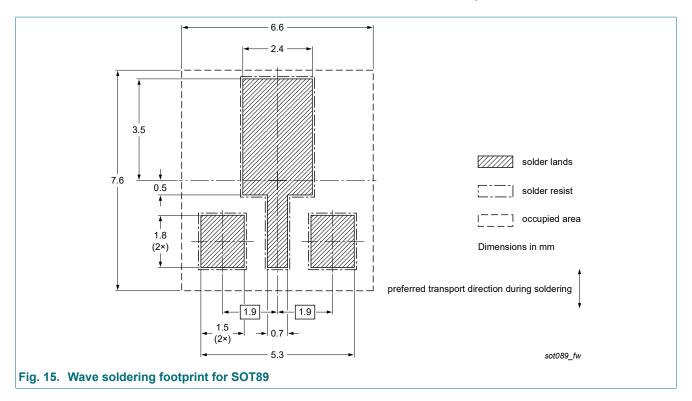
12. Package outline



13. Soldering



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14. Revision history

Table 8. Revision history

- table of the test of the tes							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PBSS4520X v.3	20240119	Product data sheet	-	PBSS4520X v.2			
Modifications:	 The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. 						
PBSS4520X v.2	20041108	Product data sheet	-	PBSS4520X v.1			
PBSS4520X v.1	20040611	Product data sheet	-	-			

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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